

insulator which acts as a potential barrier for the charge storage nodes, wherein said charge storage node is located between said control gate and said current path;

wherein said plurality of semiconductor memory devices stores information by a difference of an electron charge stored in each said charge storage node;

a plurality of control gates connected to each other between a plurality of said semiconductor memory devices; and

wherein a voltage applied between the source and the drain region in the semiconductor memory device is different according to the difference in information to be written in a writing operation for different information stored in each of said plurality of semiconductor memory device.

B'
cont.

38. (Amended) The semiconductor memory apparatus according to claim 37, wherein a large voltage among the voltage applied between the source and the drain regions in the semiconductor memory devices is over 3 V in the writing operation of the information.

39. (Amended) The semiconductor memory device according to claim 37, wherein a small voltage among the voltage applied between the source and the drain regions in the semiconductor memory devices is substantially 0 V in the writing operation of the information.

B' 40. (Amended) The semiconductor memory device according to claim 37, wherein a positive/negative polarity of the voltage applied between the source and the drain regions in a reading operation to read a stored information is opposite from a positive/negative polarity of the voltage applied between the source and the drain regions in the writing operation.

41. (Amended) The semiconductor memory device according to claim 37, wherein the source and drain regions and the current path is located on an insulator film.

REMARKS

Claims 37-41 have been amended. No claims have been canceled or added. Accordingly, claims 37-41 are currently pending in the application.

RESTRICTION REQUIREMENT

Applicants request reconsideration of the restriction requirement since all of the claims are directed to an apparatus. Applicants elect the apparatus claims in order to provide a complete reply.